TOSHIBA Field Effect Transistor Silicon N Channel Junction Type

2SK211

FM Tuner Applications VHF Band Amplifier Applications

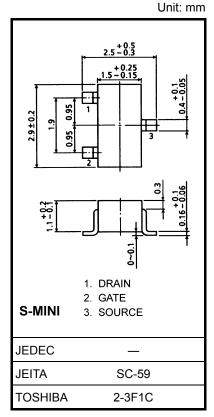
- Low noise figure: NF = 2.5dB (typ.) (f = 100 MHz)
- High forward transfer admitance: $|Y_{fs}| = 9 \text{ mS (typ.)}$
- Extremely low reverse transfer capacitance: $C_{rss} = 0.1 \text{ pF (typ.)}$

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Gate-drain voltage	V_{GDO}	-18	V
Gate current	IG	10	mA
Drain power dissipation	P _D	150	mW
Junction temperature	Tj	125	°C
Storage temperature range	T _{stg}	−55~125	°C

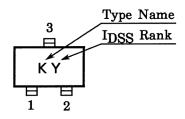
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



Weight: 0.012 g (typ.)

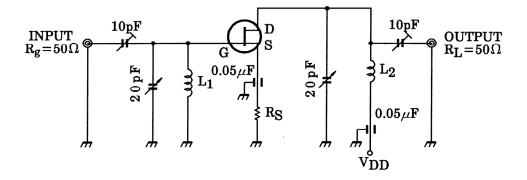
Marking



Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = -0.5 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	-10	nA
Gate-drain breakdown voltage	V (BR) GDO	$I_G = -100 \mu A$	-18	_	_	V
Drain current	I _{DSS} (Note)	V _{GS} = 0 V, V _{DS} = 10 V	1.0	_	10	mA
Gate-source cut-off voltage	V _{GS} (OFF)	$V_{DS} = 10 \text{ V}, I_D = 1 \mu A$	-0.4	_	-4.0	V
Forward transfer admittance	Y _{fs}	$V_{GS} = 0 \text{ V}, V_{DS} = 10 \text{ V}, f = 1 \text{ kHz}$	_	9	_	mS
Input capacitance	C _{iss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		6.0	_	pF
Reverse transfer capacitance	C _{rss}	V _{GD} = -10 V, f = 1 MHz	_	_	0.15	pF
Power gain	G _{PS}	V _{DD} = 10 V, f = 100 MHz (Figure)	_	18	_	dB
Noise figure	NF	V _{DD} = 10 V, f = 100 MHz (Figure)		2.5	3.5	dB

Note: I_{DSS} classification O: 1.0~3.0 mA, Y: 2.5~6.0 mA, GR (G): 5.0~10.0 mA

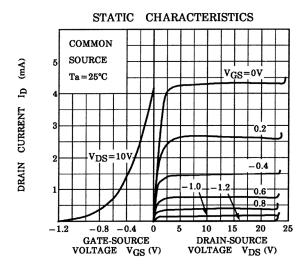


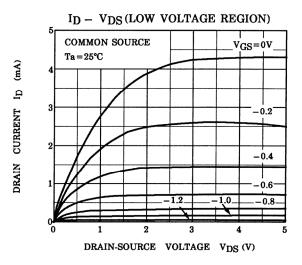
 $L_{1}{:}~0.8~mm\varphi~Ag~PLATED~Cu~WIRE~3~TURNS,~10~mm~ID,~10~mm~LENGTH$ $L_{2}{:}~0.8~mm\varphi~Ag~PLATED~Cu~WIRE~3.5~TURNS,~10~mm~ID,~10~mm~LENGTH$

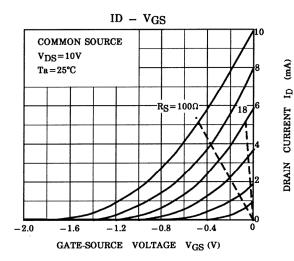
Figure 100 MHz G_{PS}, NF Test Circuit

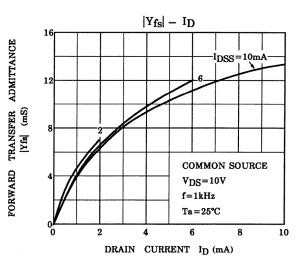
2SK211 is measured at each group by changing $R_{\rm S}.$

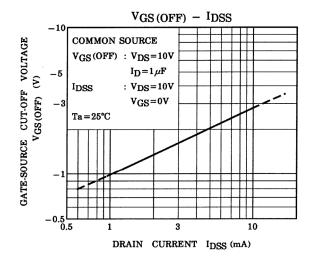
Group	RS (Ω)	
2SK211-O	0	
2SK211-Y	18 $\Omega \pm 5\%$	
2SK211-GR	100 $\Omega \pm 5\%$	

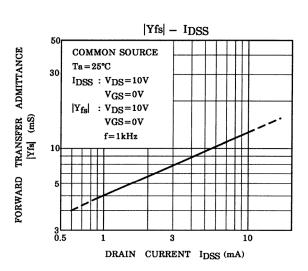




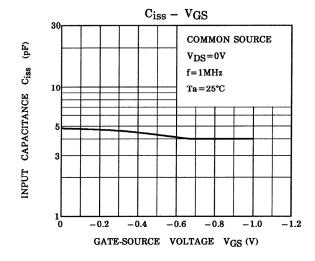


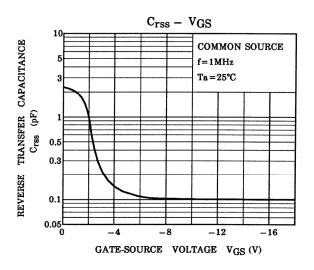


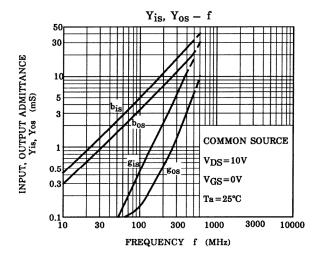


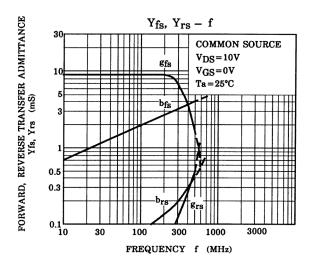


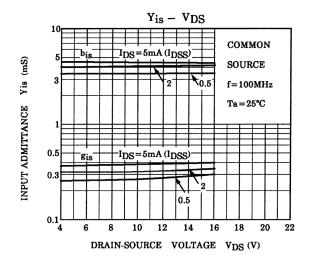
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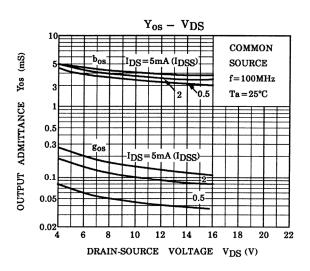


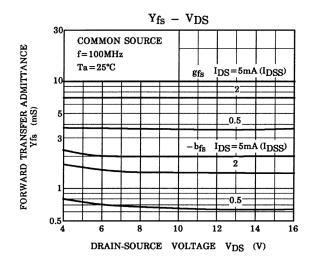


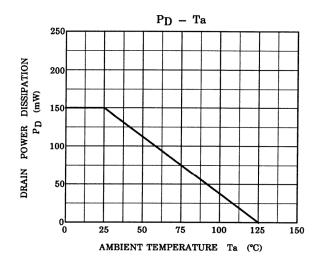












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20070701-EN GENERAL

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